

## PI Sheet

## **B-Mount**

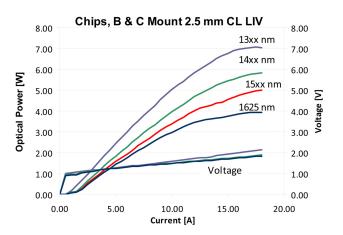
High Power Single-Mode and Multi-Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

- ApplicationsOEM MedicalDPSS pump source
- Lidar .
- Military / Aerospace
- Features .
- Cost effective High Output Power .
- . High Dynamic Range
- High EfficiencyStandard Low Cost Package



SemiNex delivers the highest available power at infrared wavelengths between 12xxnm and 16xxnm as well 19xxnm to 24xxnm. When necessary we will further optimize the design of our InP or GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.





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PI Sheet



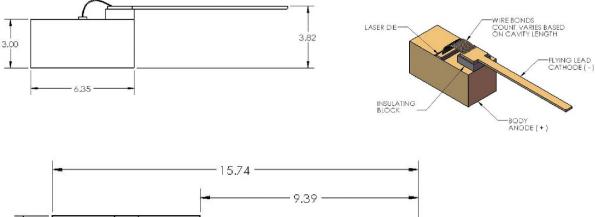


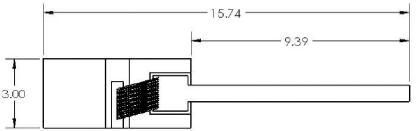
	Symbol	B-123	Units
Optical			
Wavelength	λ <sub>c</sub>	1350	nm (±20)
Output Power (CW)	P。	5.60	watts (±10%)
Chip Cavity Length	CL	2500	μm
Emitter Width	W	95	μm
Emitter Height	Н	1	μm
Spectral Width	δλ	15	nm 3dB
Slope Efficiency	η∘	0.40	W/A
Fast Axis Div.*	Θ_perp	28	deg FWHM
Slow Axis Div.	O_parallel	9	deg FWHM
Electrical			
Power Conversion Eff.	η	22	%
Threshold Current	I <sub>th</sub>	0.5	A
Operating Current	I <sub>op</sub>	14	A
Operating Voltage	V <sub>op</sub>	1.8	V
Mechanical			
Weight		0.5	g
Operating Temp.**		-40 to 85	°C
Storage Temp.		-40 to 85	°C
Operating Voltage Min.		1.8	V
Operating Voltage Max.		2	V

**B-Mount** 

Specified values are rated at a constant heat sink temperature of 20°C. \*\*Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal. \*Fast Axis Divergence can be changed with lens option.







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DANGER LE / INVISIBLE LASER RADIATION ID DIRECT EXPOSURE TO BEAU CLASS IIIb and IV LASER PRODUCTS This product complies with 2/CFR1040 as applicab Laser aperture is on the test station. Later radiation from this product is considered an acute hazard to t skin and eyes.